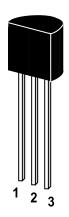
NPN Silicon Epitaxial Planar Transistor

Low frequency amplifier applications.

The transistor is subdivided into three group, B, C and D according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	100	mA
Emitter Current	I _E	-100	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°С
Storage Temperature Range	Ts	-55 to +150	оС







ST 2SC458

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V_{CE} =12V, I_{C} =2mA					
Current Gain Group B	h _{FE}	100	-	200	-
С	h _{FE}	160	-	320	-
D	h _{FE}	250	-	500	-
Collector Cutoff Current					
at V _{CB} =18V	I _{CBO}	-	-	0.5	μΑ
Emitter Cutoff Current					
at V _{EB} =2V	I _{EBO}	-	-	0.5	μΑ
Collector Emitter Saturation Voltage					
at I _C =10mA, I _B =1mA	V _{CE(sat)}	-	-	0.2	V
Transition Frequency					
at V _{CE} =12V, I _C =2mA	f⊤	-	230	-	MHz
Base Emitter Voltage					
at I _C =2mA, V _{CE} =12V	V_{BE}	-	0.67	0.75	V
	52				
Collector Output Capacitance at V _{CB} =10V, f=1MHz	C _{OB}	_	1.8	3.5	pF
	ООВ		1.0	0.0	Pi
Collector Base Breakdown Voltage	.,	00			.,
at I _C =10μA	V _{CBO}	30	-	-	V
Collector Emitter Breakdown Voltage					
at I _C =1mA	V _{CEO}	30	-	-	V
Emitter Base Breakdown Voltage					
at I _C =10μA	V_{EBO}	5	-	-	V
Noise Figure					
at V_{CE} =6V, I_{C} =0.1mA, f=1kHz, R_{g} =500 Ω	NF	-	4	10	dB
Small signal input impedance					
at V _{CE} =5V, I _C =0.1mA,f=270Hz					
	h _{ie}	-	16.5	-	kΩ
	h _{ie}	-	70	-	X10 ⁻⁶
	h _{ie}	-	130	-	-
	h _{ie}	-	11	-	μS



SEMTECH ELECTRONICS LTD.

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